

Characterization of Ni/SnPb - TiW/Pt Flip Chip Interconnections in Silicon Pixel Detector Modules

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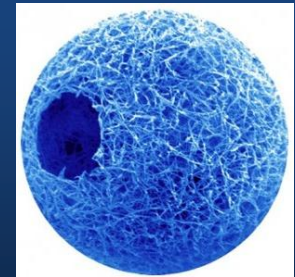
Department of Physics, University of Helsinki, Finland;
Helsinki Institute of Physics, Finland;
Advacam Ltd, Finland



Outline

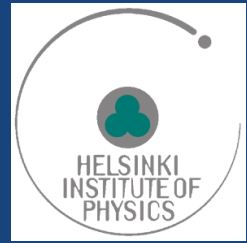


- I. Background
 - i. Silicon detectors
 - ii. Flip-chip interconnects
- II. Scanning White Light Interferometry (SWLI)
- III. Results
- IV. Conclusions

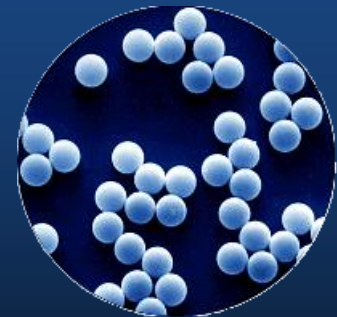




Outline



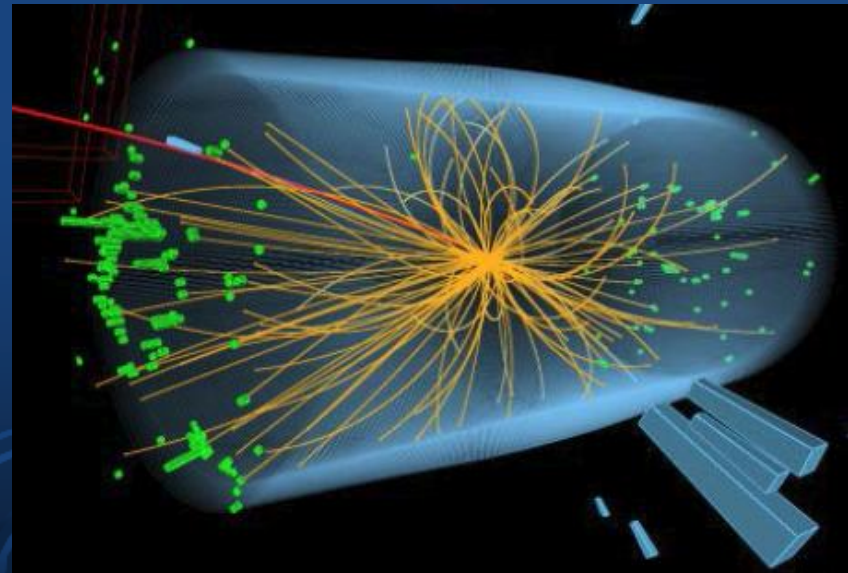
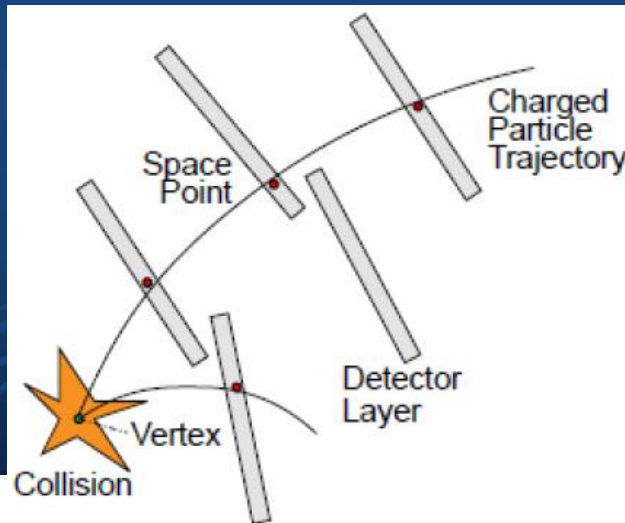
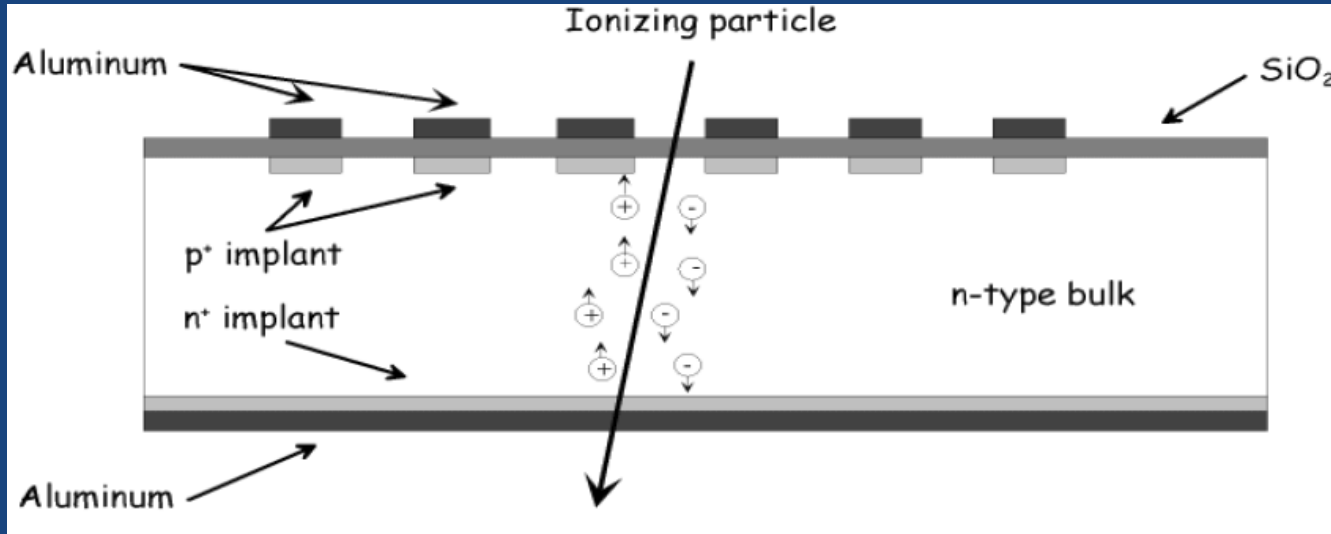
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Silicon detectors

Particle tracking

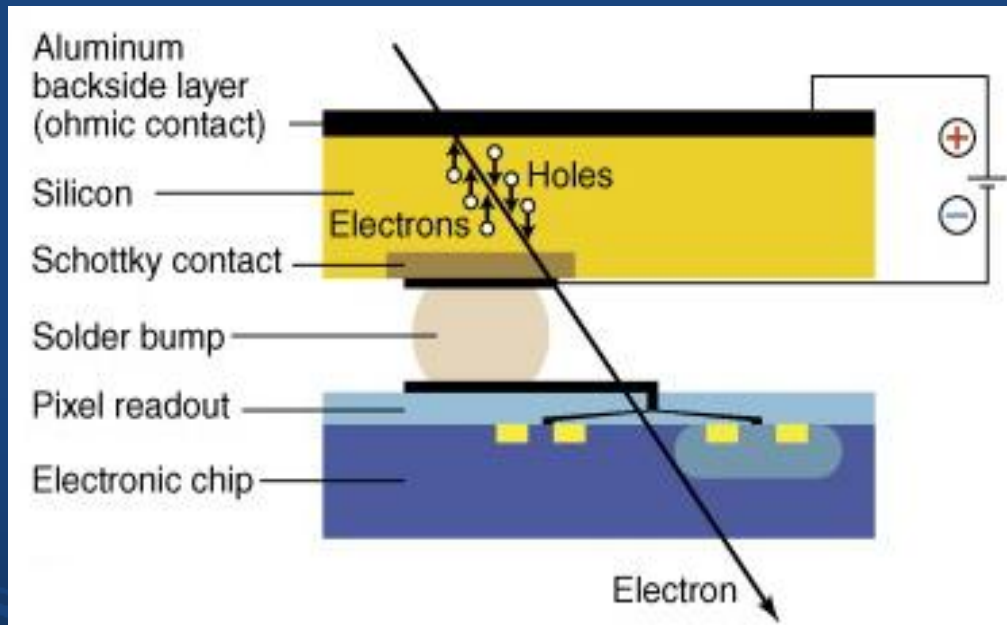




Flip – Chip Interconnects

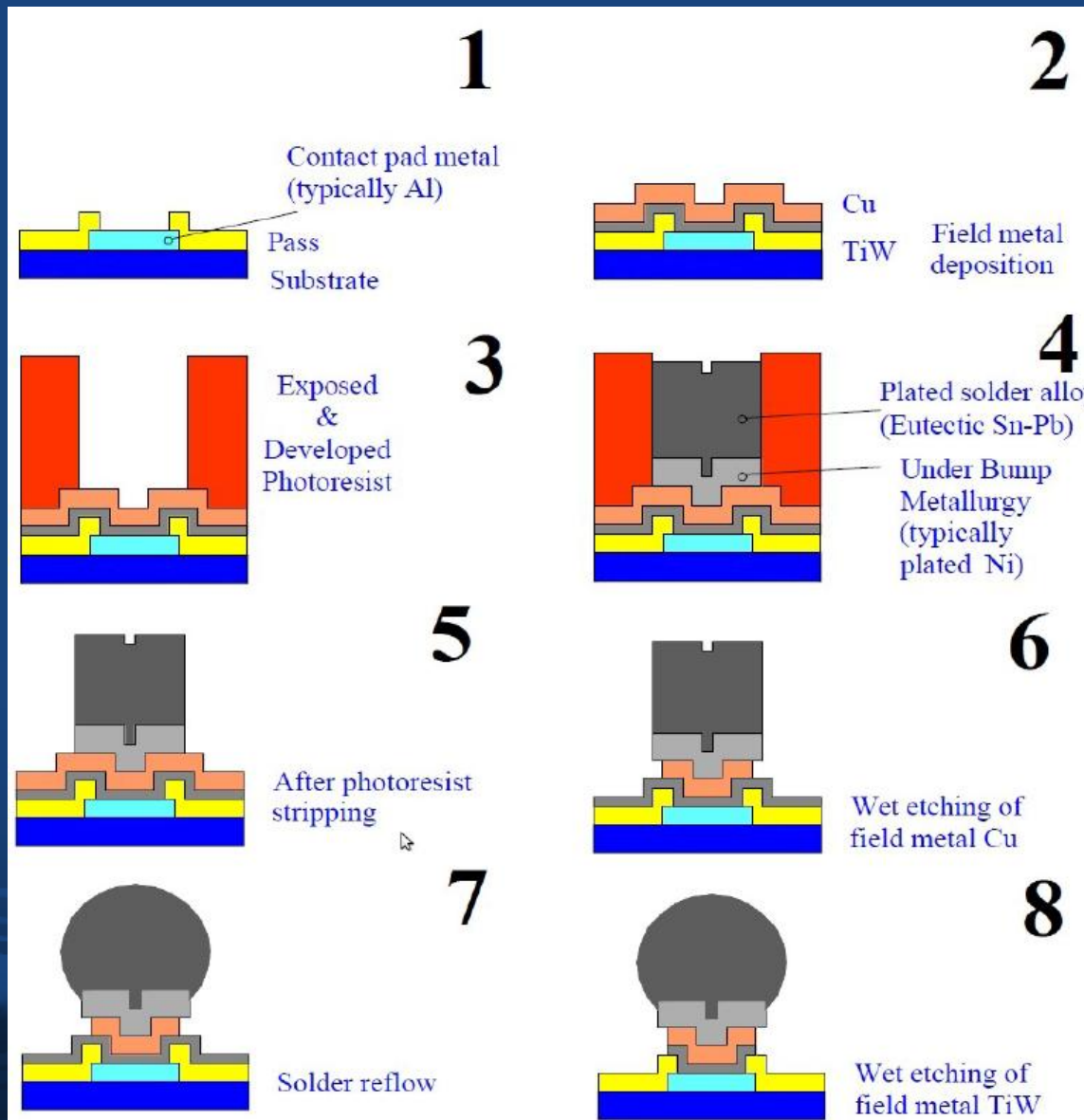
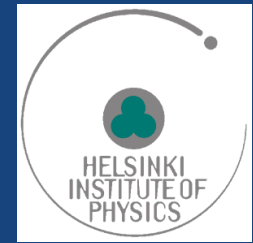


Bump-bonding is the most common way of making interconnections to external electrical circuit with bumps that have been deposited on the surface of both the chips.





Bumping process flow





CMS bare pixel module



CMS Barrel Pixel Module

Signalcable

Powercable

SMD-Components

Token bit manager

TBM

HDI High density interconnect

Sensor $16 \times 62 \text{ mm}^2$
66,560 pixels

bump bonding:

ROCs Read-out chips

SiN Basestrips

[W. Erdmann]

Module dimensions: $66.6 \times 26.0 \text{ mm}^2$

full-module $\hat{=}$ 16 ROCs





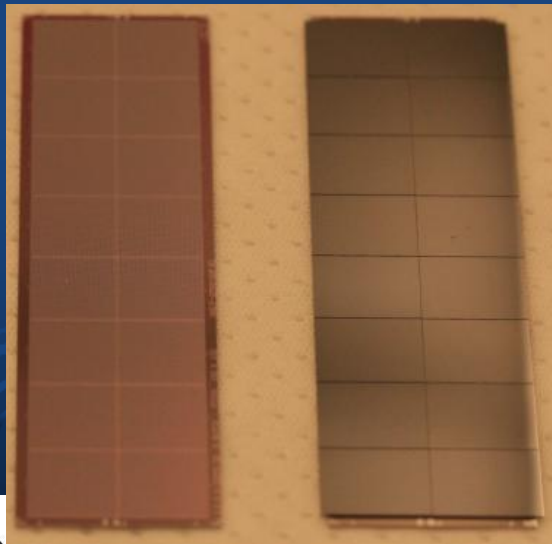
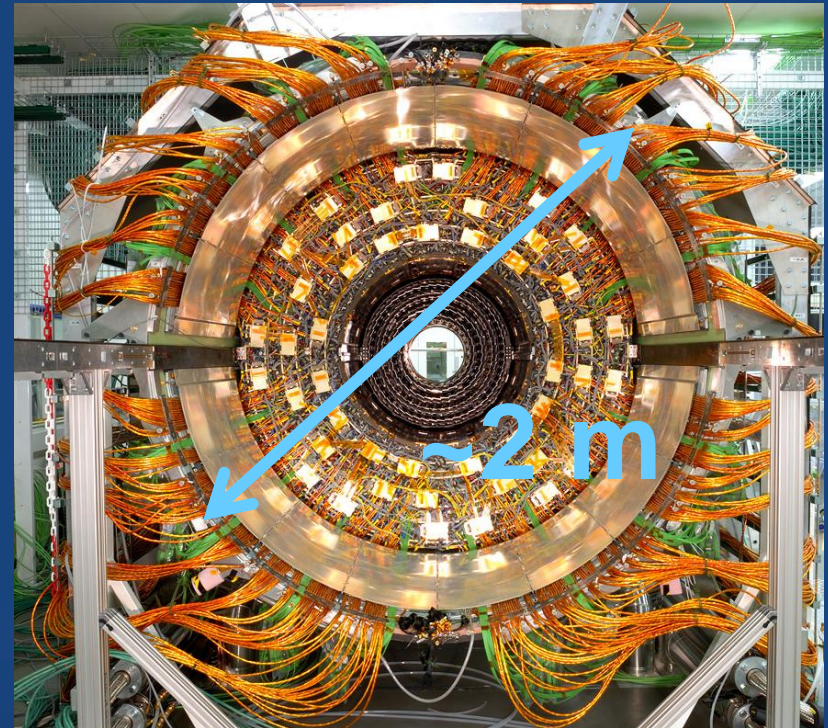
Silicon detectors

CMS bare pixel module



The CMS bare pixel module consist of a sensor and 16 Read Out Chips (ROC) bonded on sensor by Ni/SnPb solder bumps. Pt is used as Under Bump Metallization (UBM) on sensor chips.

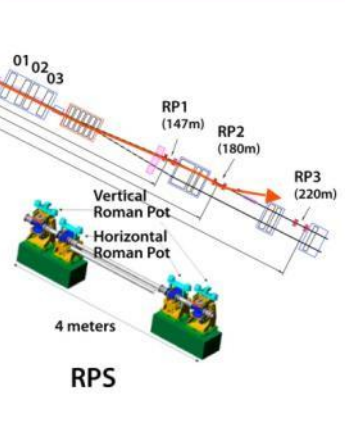
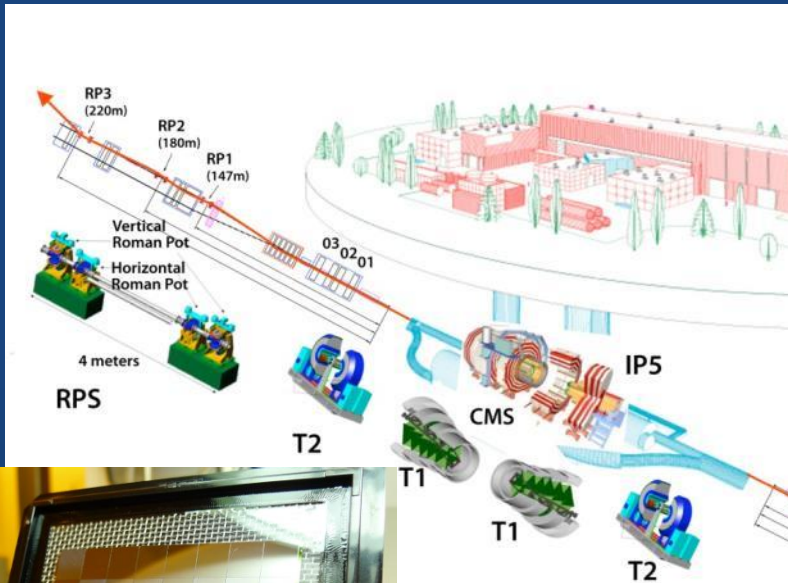
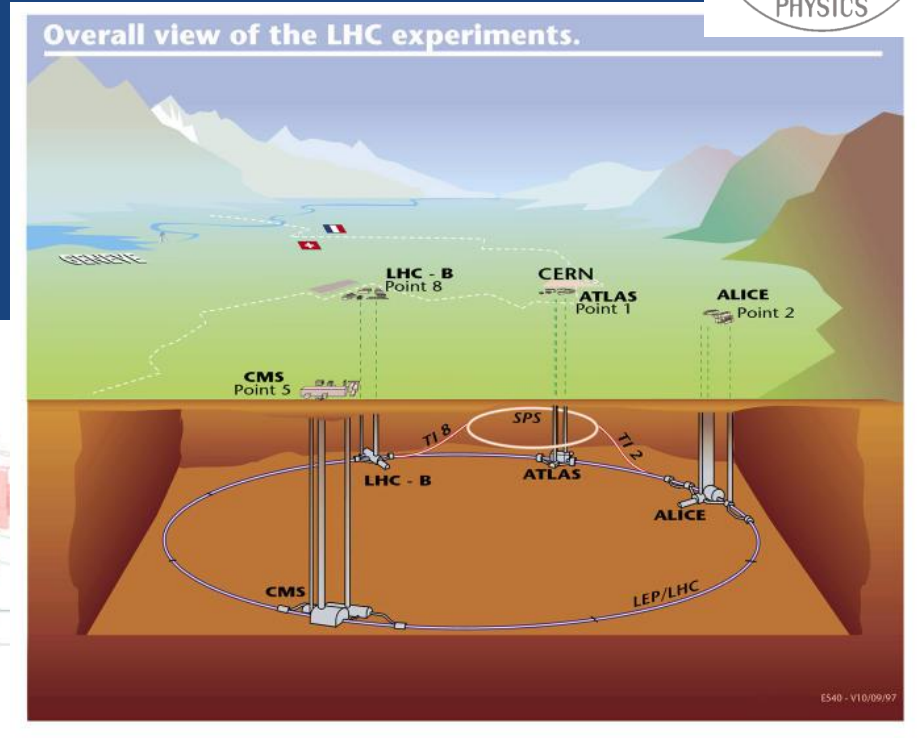
Number of pixels in a module is $16 \times 80 \times 52 = 66560$. $<0.1\%$ of dead channels is acceptable



The CMS Tracker implements 25000 silicon strip sensors covering an area of 210m². Connected to 75000 APV chips, one has to control 9600000 electronic readout channels, needing about 26 million micro bonds.

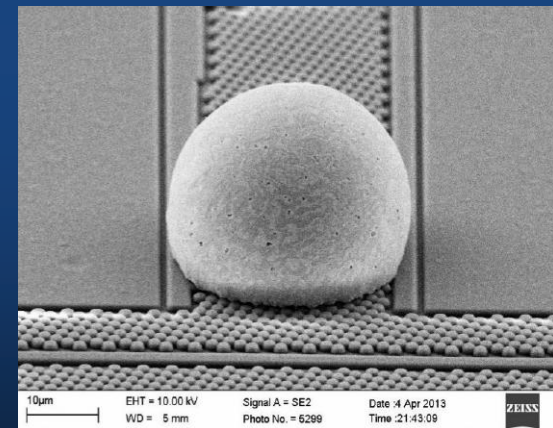
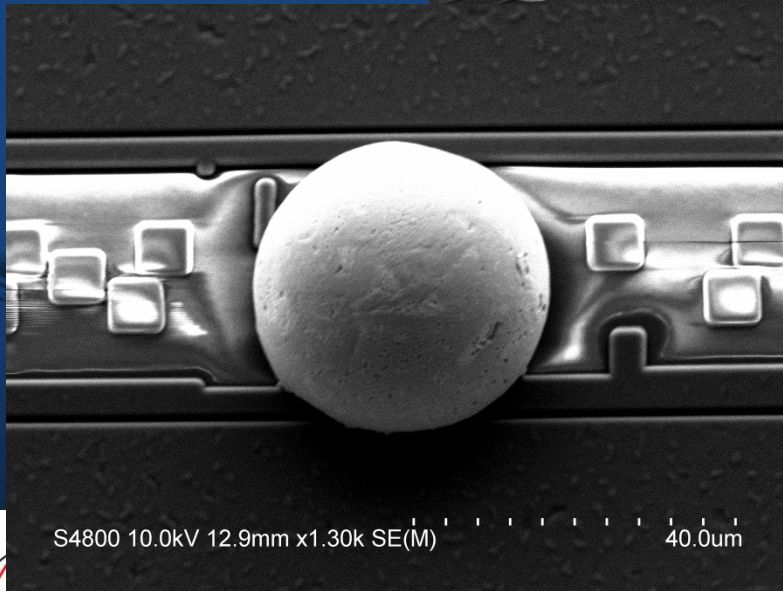
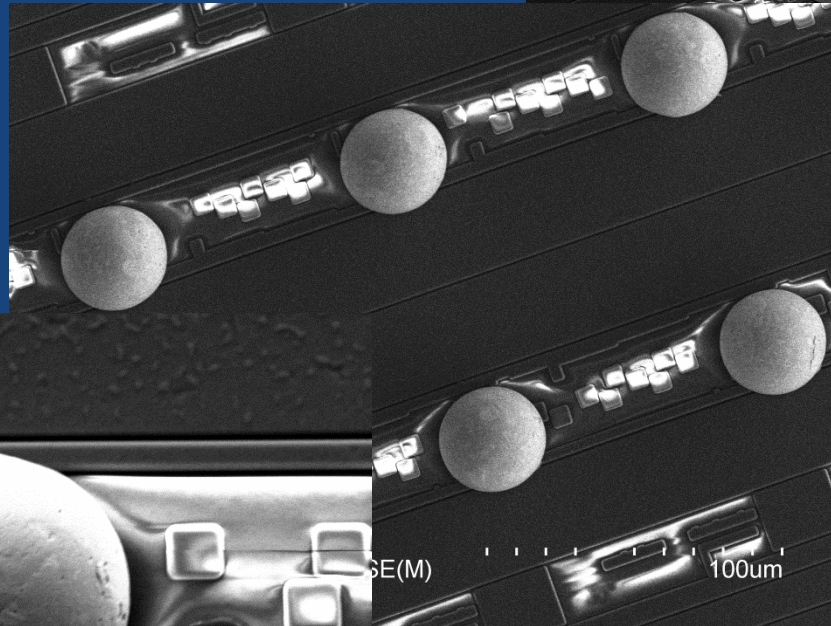
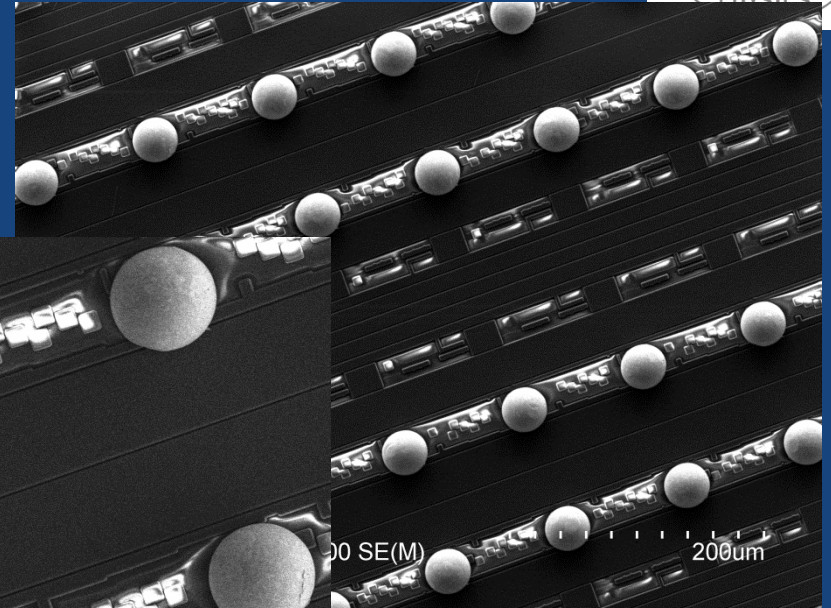


CMS Upgrade Project



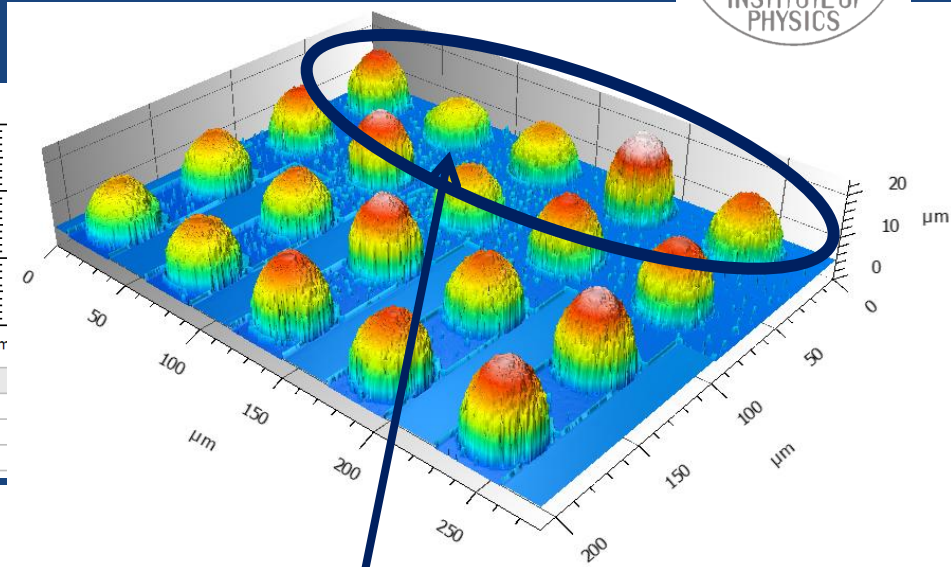
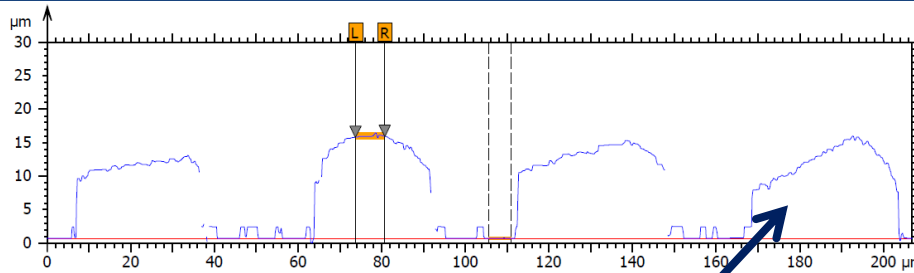


SnPb solder bumps



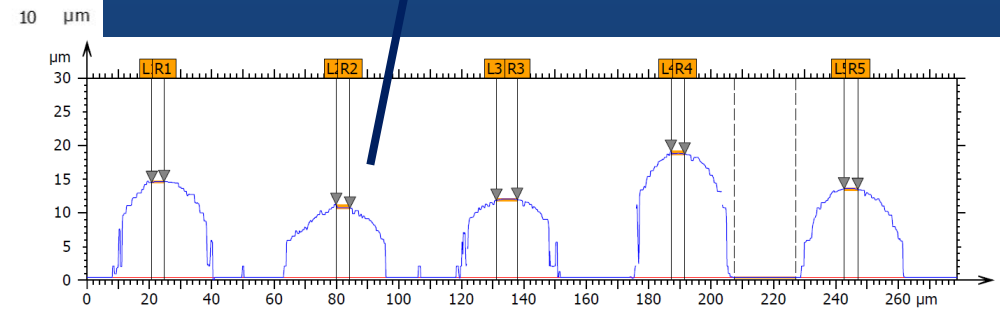
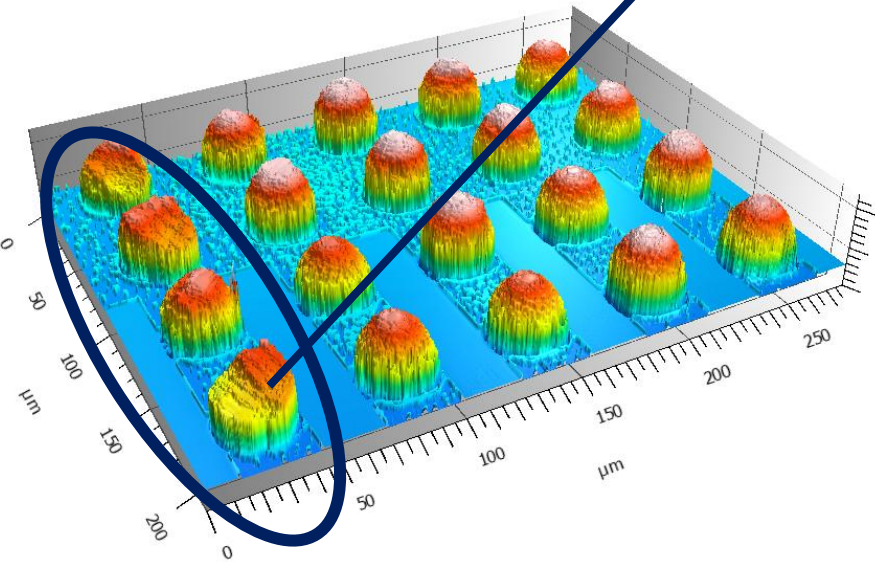


Bump - bonds Challenges



Parameters	Step 1	Unit
Width	7.06	μm
Maximum height	15.7	μm
Mean height	15.2	μm

Maximum height measurement of the bump - bonds.

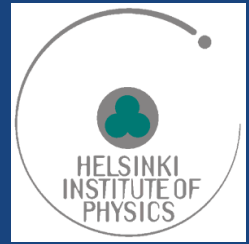


Parameters	Unit	Step 1	Step 2	Step 3	Step 4	Step 5
Width	μm	4.07	4.65	6.82	4.50	4.50
Maximum height	μm	14.2	10.9	11.6	18.7	13.2
Mean height	μm	14.2	10.4	11.6	18.4	13.2

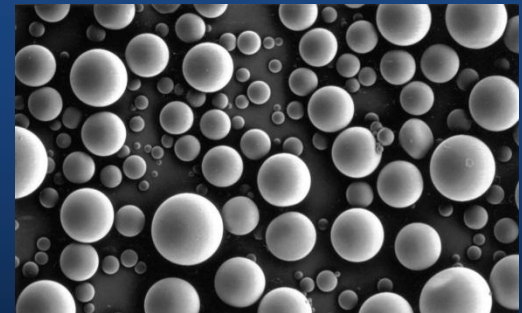




Outline

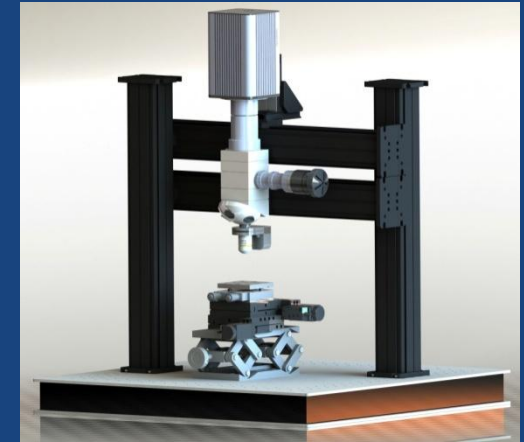
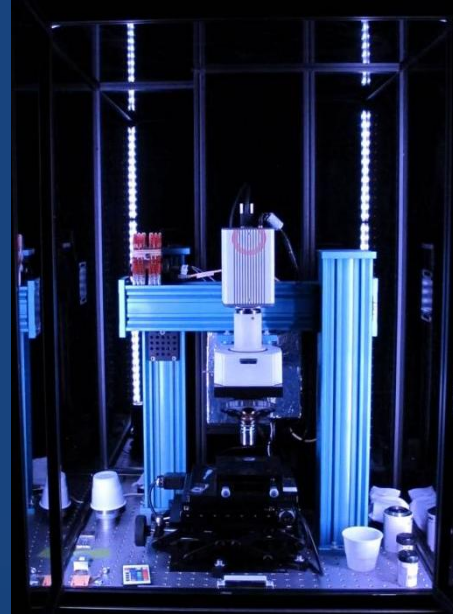
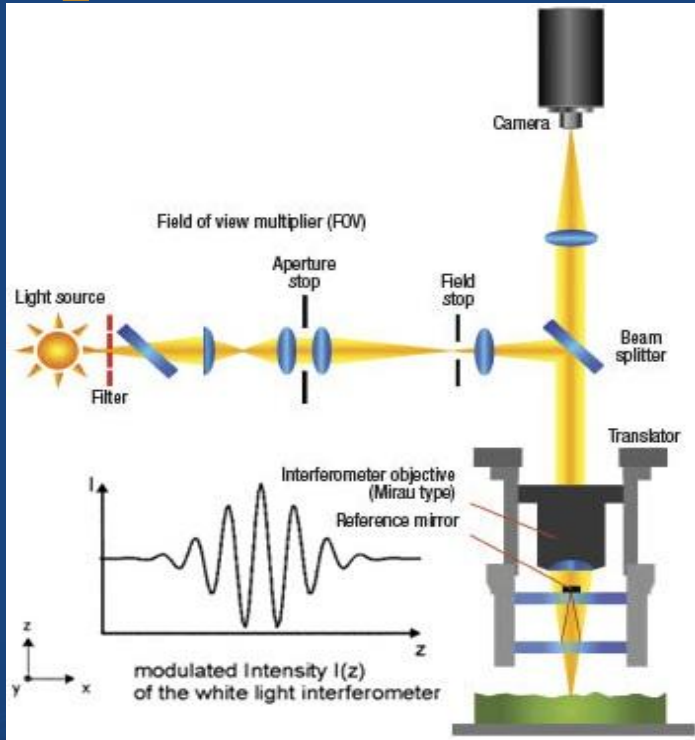


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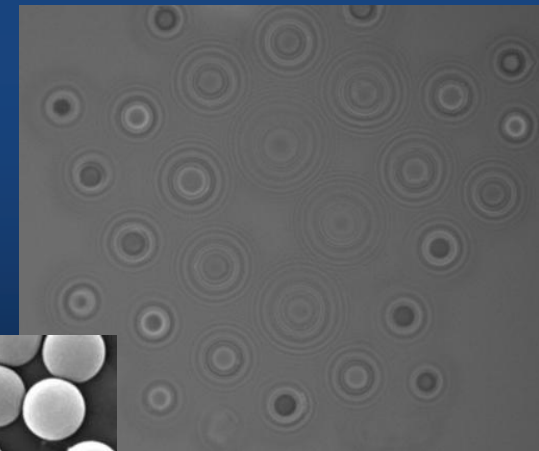
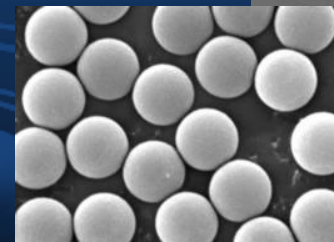


Scanning White Light Interferometry (SWLI)



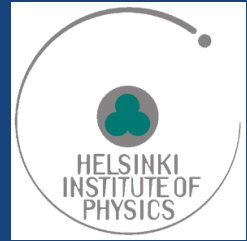
Objective: NIKON CF IC Epi Plan DI 50x 0,55NA
Total magnification: 25x (0,5x tubelens NIKON)

Camera: HAMAMTSU Orca Flash 2.8
Light source: halogen bulb

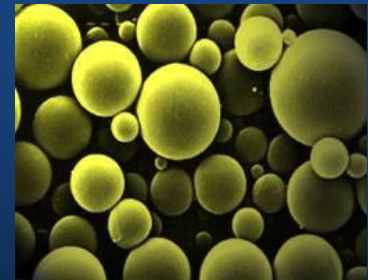




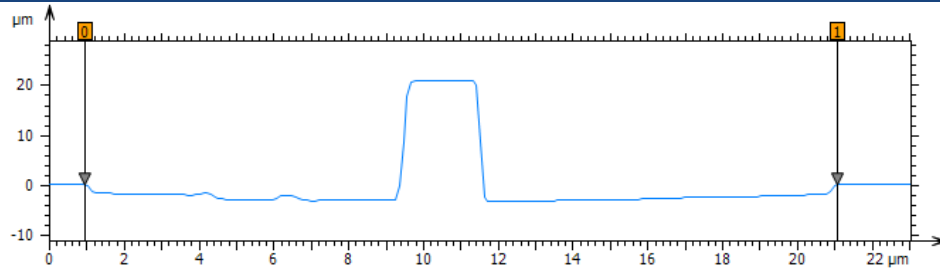
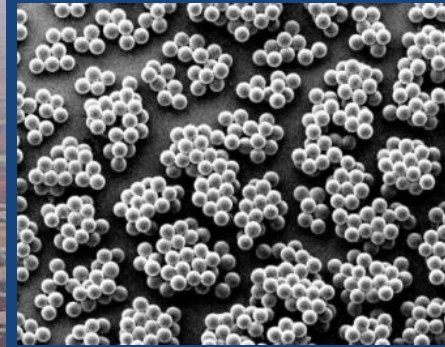
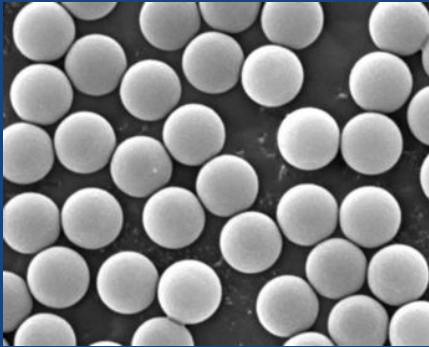
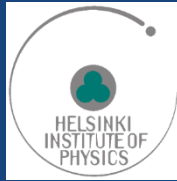
Outline



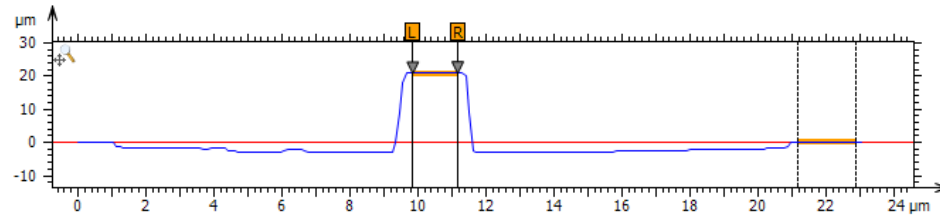
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SWLI Measurements of NIST Calibrated SiO₂ Spheres

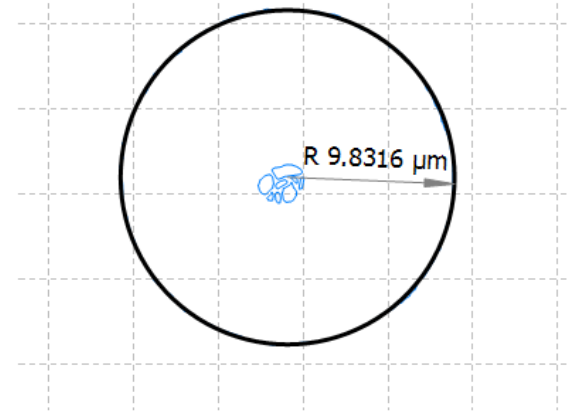


Parameters	0-1	Unit
Horizontal distance	20.1	μm
Height difference	0.00707	μm

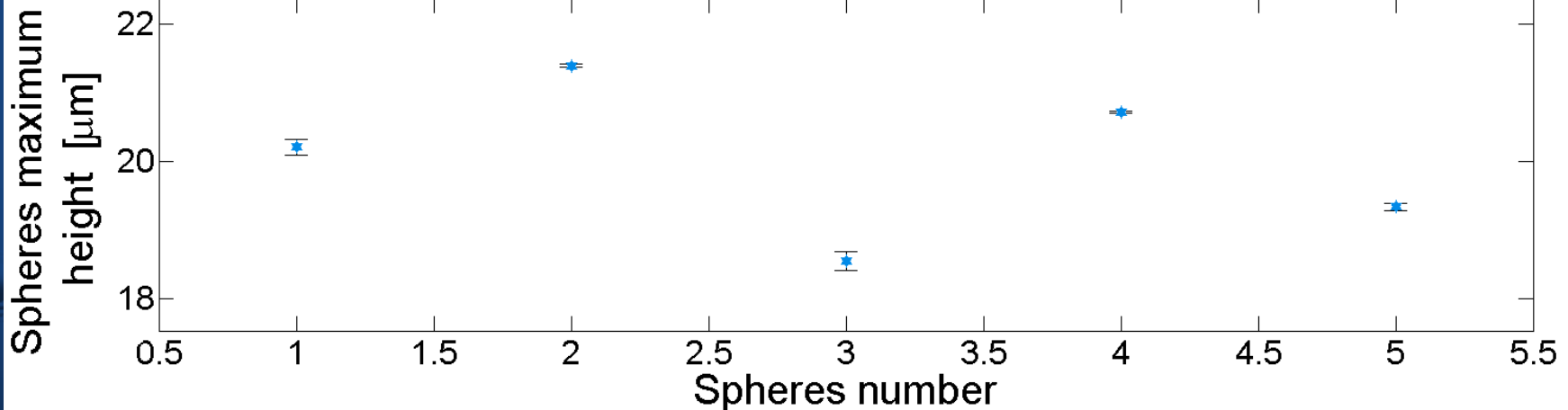
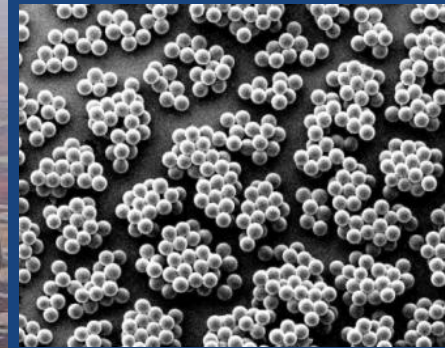
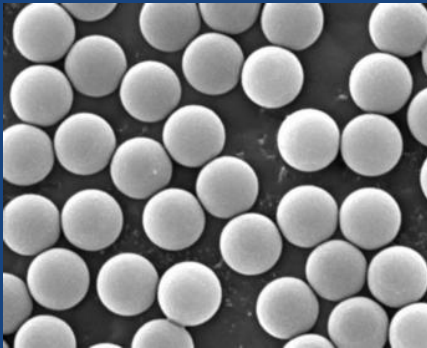


Parameters	Step 1	Unit
Width	1.44	μm
Maximum height	20.7	μm
Mean height	20.6	μm

Width, Maximum height and Radius measurement of the spheres



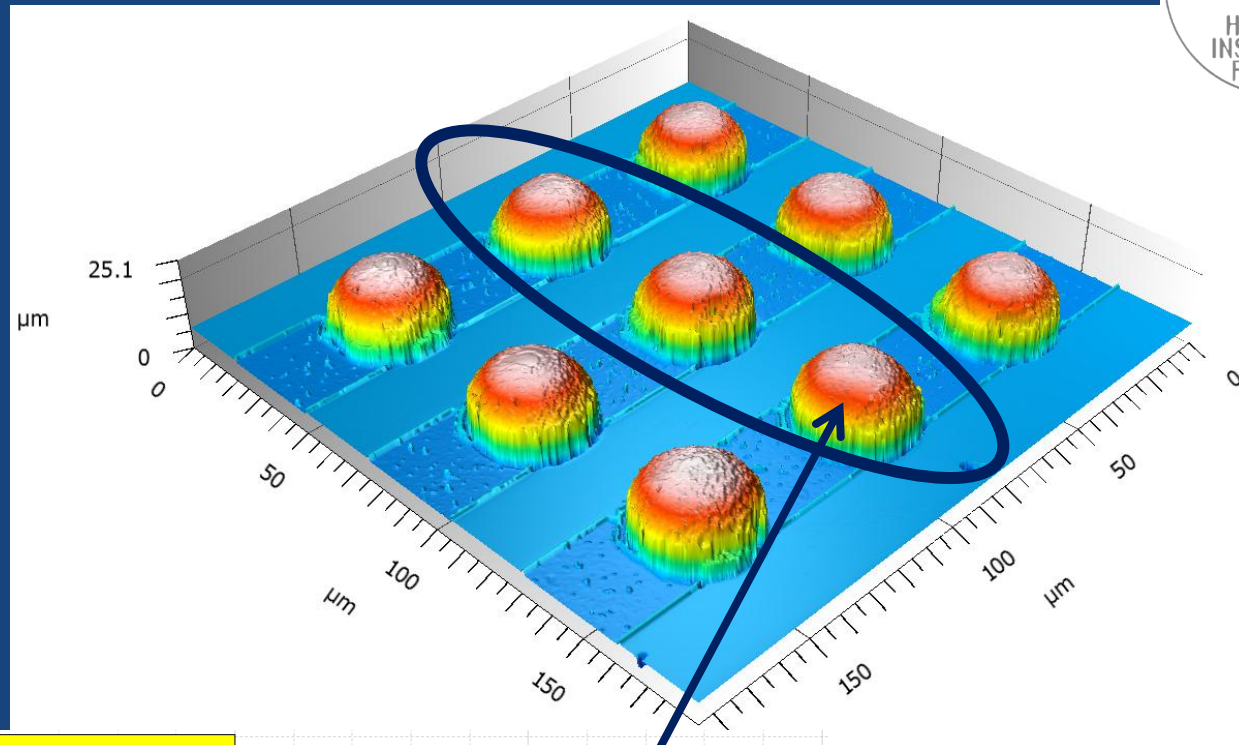
SWLI Measurements of NIST Calibrated SiO₂ Spheres



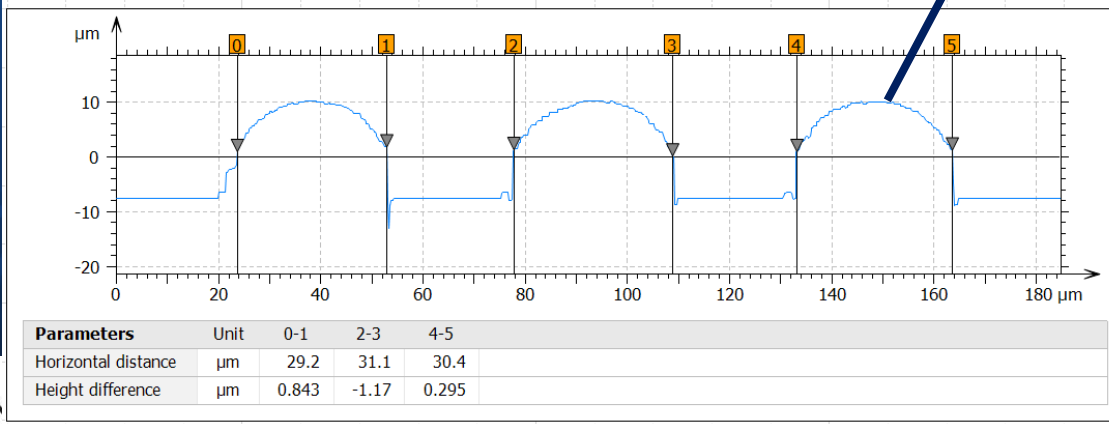
The uncertainty of the SWLI measurement at a coverage factor $k = 2$, for a 95% confidence level was $\pm 0.0076 \mu\text{m}$.



SWLI Results – Bump bonds



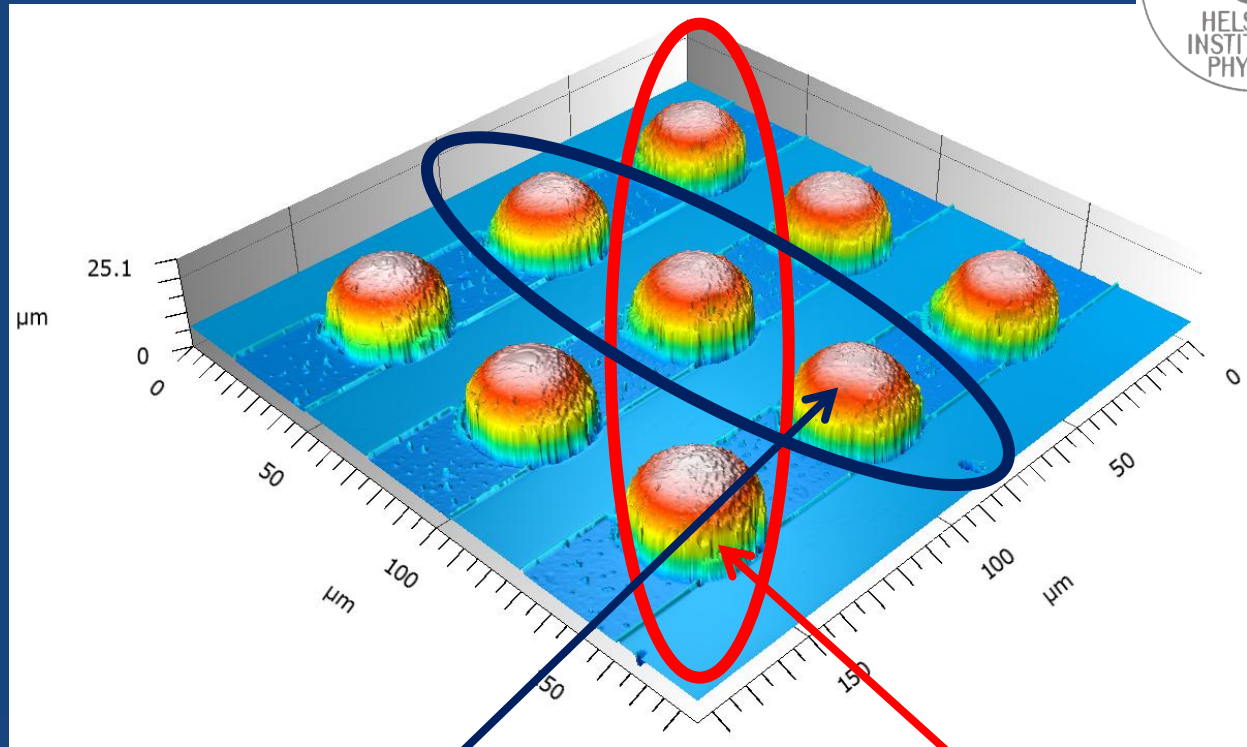
2 row - 4, 5, 6 BB Profile Extraction - West_East



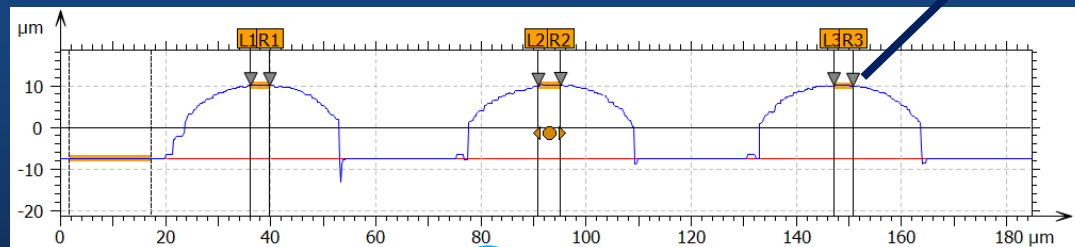
Width measurement of the bump - bonds.



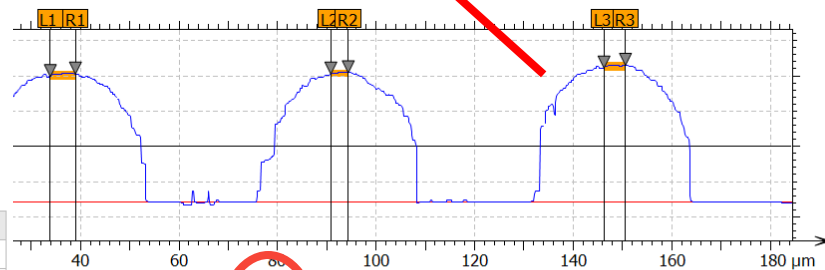
SWLI Results – Bump bonds



Maximum height measurement of the bump - bonds.



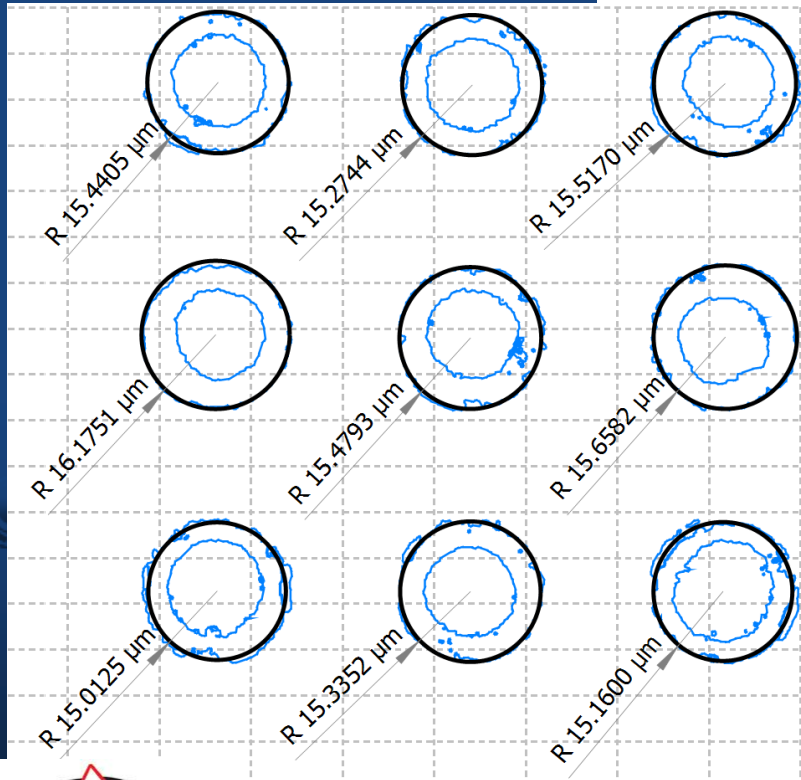
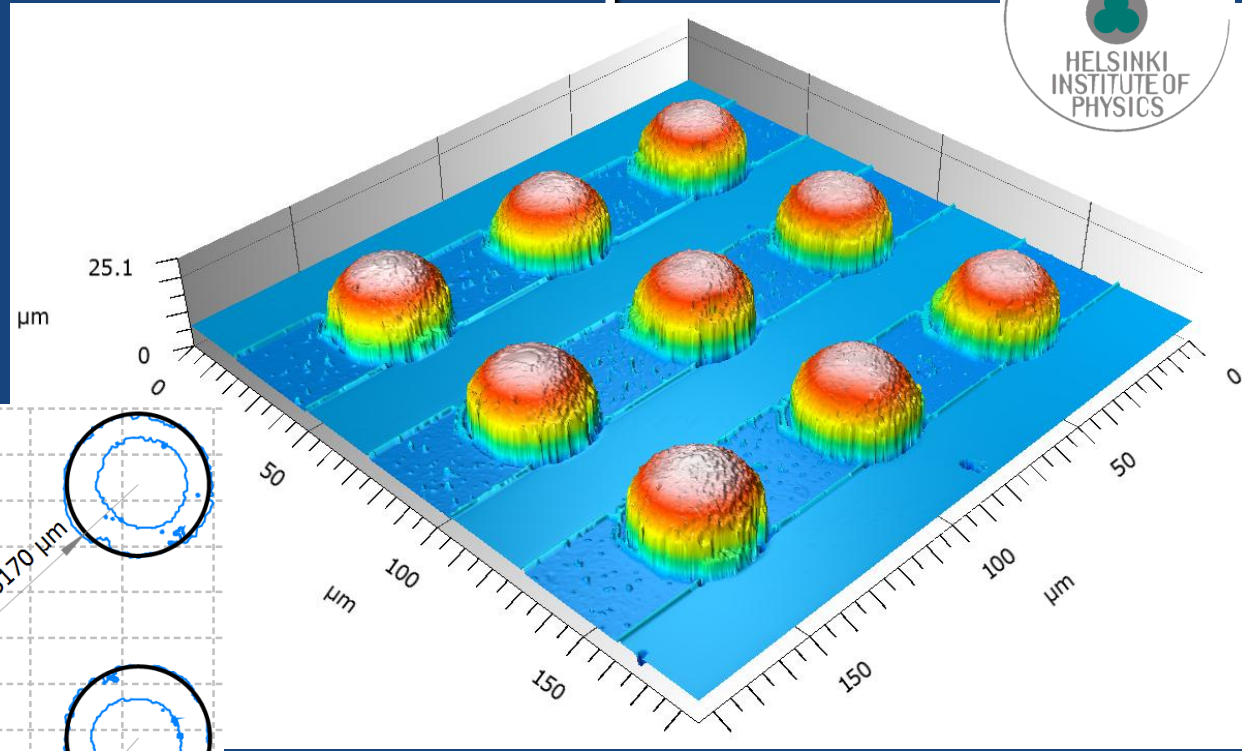
Parameters	Unit	Step 1	Step 2	Step 3
Width	μm	3.78	4.36	3.78
Maximum height	μm	17.7	17.8	17.6
Mean height	μm	17.7	17.7	17.6



Unit	Step 1	Step 2	Step 3	
μm	5.23	3.63	4.50	
Maximum height	μm	18.2	18.4	19.4
Mean height	μm	18.1	18.3	19.3



SWLI Results – Bump bonds



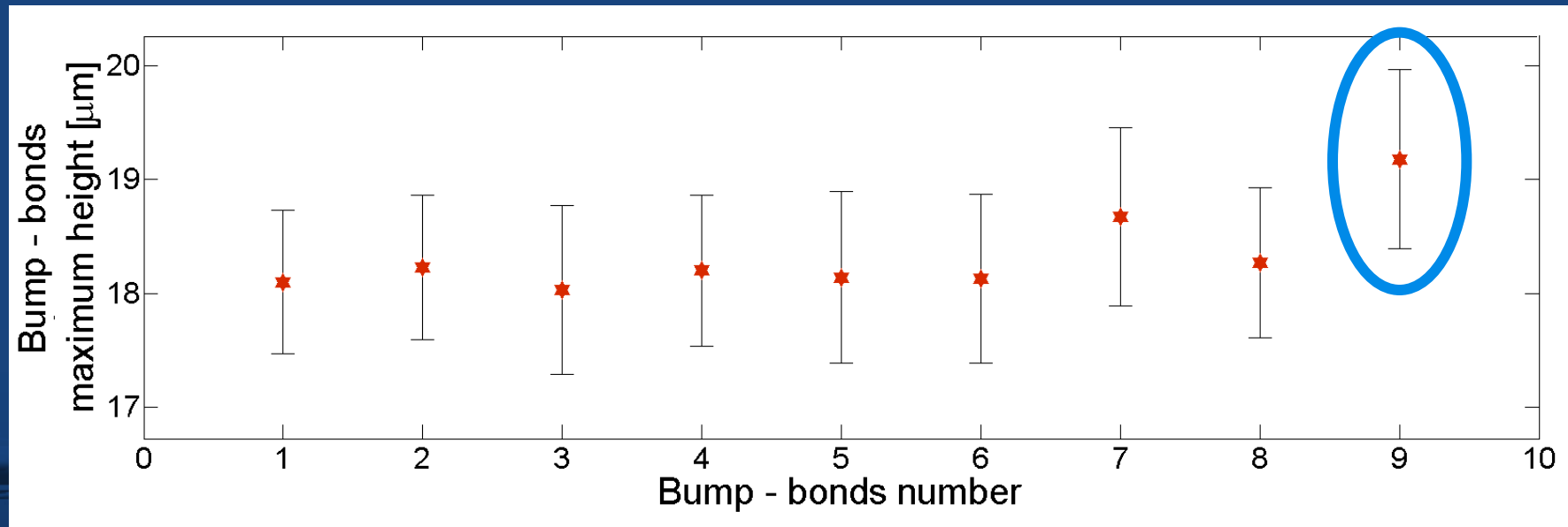
Radius measurement of the bump - bonds.



Results – Multiple bonds comparison



Maximum height measurement of the bump - bonds.

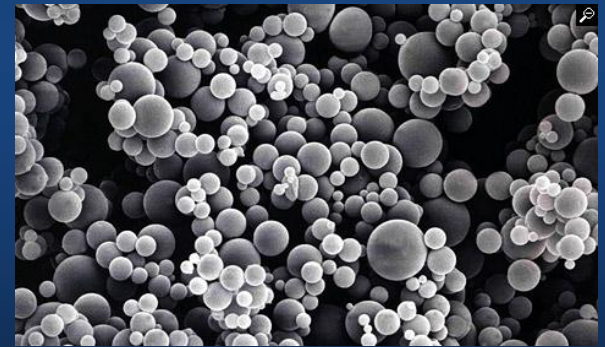




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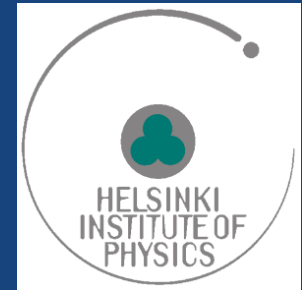




Conclusions

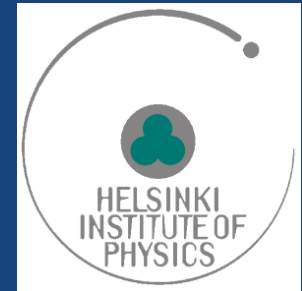


- The SWLI measurements of NIST calibrated SiO₂ Spheres was successfully made.
- The uncertainty of the SWLI measurement at a coverage factor $k = 2$, for a 95% confidence level was $\pm 0.0076 \mu\text{m}$.
- The Bump - bonds heights are in the range of 18.03 – 19.18 μm and corrections were calculated according to the UKAS M3003 requirement.



Acknowledgements

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Thank you for your Attention

